

## SMALL SIGNAL SWITCHING DIODE

REVERSE VOLTAGE: 25 V  
CURRENT: 0.15 A

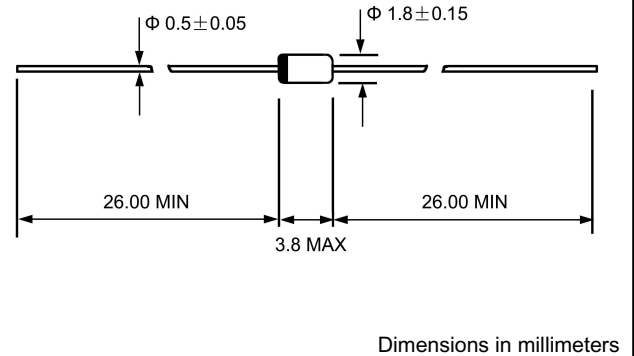
### FEATURES

- ◇ Silicon epitaxial planar diode
- ◇ High speed switching diode
- ◇ 500 mW power dissipation

### MECHANICAL DATA

- ◇ Case: DO-35, glass case
- ◇ Polarity: Color band denotes cathode
- ◇ Weight: 0.004 ounces, 0.13 grams

### DO-35



### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

#### MAXIMUM RATINGS

|  |             | 1N4154            | UNITS |
|--|-------------|-------------------|-------|
| Reverse voltage  | $V_R$       | 25                | V     |
| Peak reverse voltage   | $V_{RM}$    | 35                | V     |
| Average forward rectified current<br>half wave rectification with resistive load<br>$V_R=0V$ | $I_{F(AV)}$ | 150 <sup>1)</sup> | mA    |
| Forward surge current @ $t_F=1\mu s$   | $I_{FSM}$   | 2.0               | A     |
| Power dissipation @ $T_A=25^\circ C$   | $P_{tot}$   | 500 <sup>1)</sup> | mW    |
| Junction temperature   | $T_J$       | 175               | °C    |
| Storage temperature range  | $T_{STG}$   | -55 --- +175      | °C    |

1)Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.

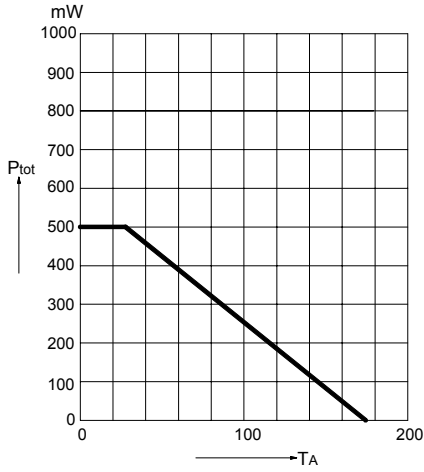
#### ELECTRICAL CHARACTERISTICS

|  |                 | MIN  | TYP | MAX               | UNITS |
|--|-----------------|------|-----|-------------------|-------|
| Forward voltage @ $I_F=30mA$   | $V_F$           | -    | -   | 1.0               | V     |
| Leakage current<br>@ $V_R=25V$   | $I_R$           | -    | -   | 100               | nA    |
|  | $I_R$           | -    | -   | 100               | μA    |
| Capacitance @ $V_R=0V, f=1MHz, V_{HF}=50mV$  | $C_J$           | -    | -   | 4.0               | pF    |
| Reverse breakdown voltage<br>tested with 5μA pulses  | $V_{(BR)R}$     | 35   | -   | -                 | V     |
| Reverse recovery time<br>from $I_F=10mA$ to $I_R=10mA$ to $I_R=1mA$<br>from $I_F=10mA$ to $I_R=1mA, V_R=6V, R_L=100\Omega$ . | $t_{rr}$        | -    | -   | 4                 | ns    |
|  |                 |      |     | 2                 | ns    |
| Thermal resistance junction to ambient   | $R_{\theta JA}$ |      |     | 500 <sup>1)</sup> | K/W   |
| Rectification efficiency @ 100MHz, $V_{RF}=2V$   | $\eta_V$        | 0.45 | -   | -                 | -     |

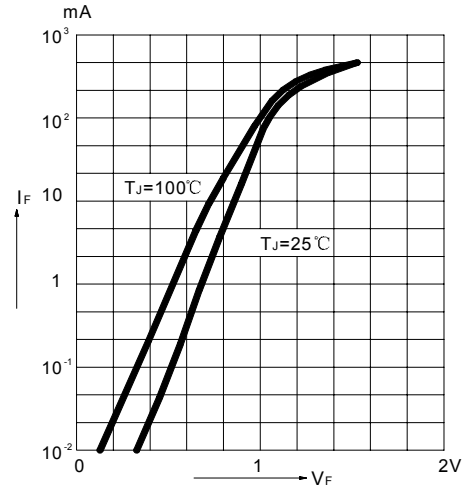
1)Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.

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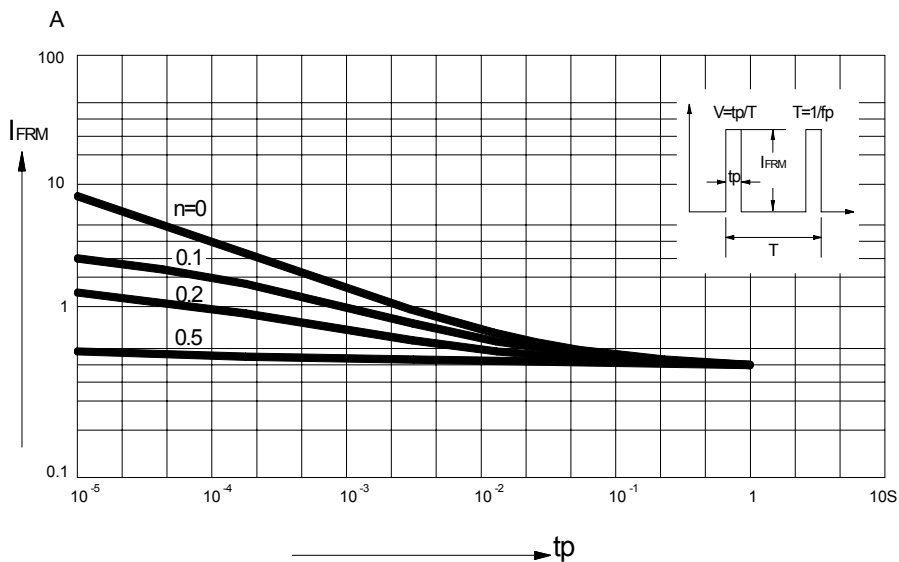
**FIG.1 – ADMISSIBLE POWER DISSIPATION  
VERSUS AMBIENT TEMPERATURE**



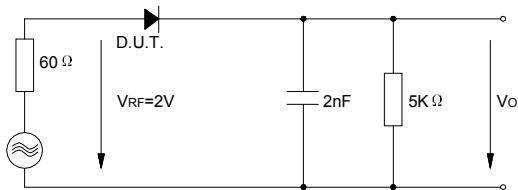
**FIG.2 – FORWARD CHARACTERISTICS**



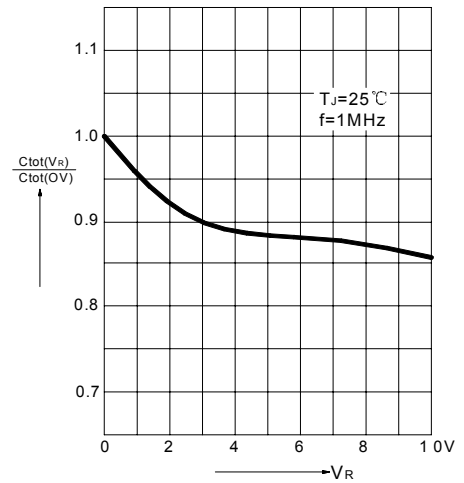
**FIG.3 – ADMISSIBLE REPETITIVE PEAK FORWARD CURRENT VERSUS PULSE DURATION**



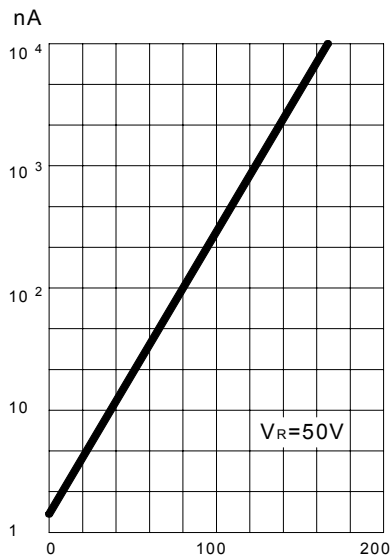
**FIG.4 – RECTIFICATION EFFICIENCY MEASUREMENT CIRCUIT**



**FIG.5 – RELATIVE CAPACITANCE VERSUS VOLTAGE**



**FIG.6 – LEAKAGE CURRENT VERSUS JUNCTION TEMPERATURE**



**FIG.7 – DYNAMIC FORWARD RESISTANCE VERSUS FORWARD CURRENT**

